

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	105001	((field adj effect adj transistor) fet mosfet) and (method process)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:35
L2	23052	((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:35
L3	8562	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/12/27 06:35
L4	762	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and ((high adj1 dielectric) "high-k")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:35
L5	846	((high near1 dielectric near1 constant) "high-k") with (hafnium zirconium hfo zro)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:36
L6	846	((high near1 dielectric near1 constant) "high-k") with (hafnium zirconium hfo zro)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:36
L7	137	(((((field adj effect adj transistor) fet mosfet) and (method process)) and (fabricating fabricated) and gate and drain and source) and (channel near1 region)) and (((high adj1 dielectric) "high-k") with (hafnium zirconium hfo zro))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:37
L8	10	7 and nitrate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:42
L9	1	"6013553".pn. and temperature	US-PGPUB; USPAT; EPO; JPO	OR	ON	2004/12/27 06:43